

BCV62

PNP general-purpose double transistors Rev. 4 — 26 July 2010

Product data sheet

Product profile

1.1 General description

PNP general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package		NPN complement
	NXP	JEITA	
BCV62	SOT143B	-	BCV61
BCV62A			BCV61A
BCV62B			BCV61B
BCV62C	_		BCV61C

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-100	mΑ
Transisto	r TR1					
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	100	-	-	
		$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$	100	-	800	



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 Table 2.
 Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Transistor	TR2					
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -2 \text{ mA}$				
BCV62A BCV62B BCV62C	BCV62		100	-	800	
		100	-	250		
	BCV62B		220	-	475	
	BCV62C		420	-	800	

2. Pinning information

Table 3. Pinning

Table 3.	rinning		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2	4 3	4 3
2	collector TR1		
3	emitter TR1		TR2
4	emitter TR2	1 2	1 2
			006aaa843

3. Ordering information

Table 4. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BCV62	· -	plastic surface-mounted package; 4 leads	SOT143B			
BCV62A						
BCV62B						
BCV62C						

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BCV62	3M*
BCV62A	3J*
BCV62B	3K*
BCV62C	3L*

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• •	•		
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
V_{CBO}	collector-base voltage	open emitter	-	-30	V
V_{CEO}	collector-emitter voltage	open base	-	-30	V
V _{EBS}	emitter-base voltage	$V_{CE} = 0 V$	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I_{BM}	peak base current		-	-200	mA
Per device	e				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C
·	· · · · · · · · · · · · · · · · · · ·	·	·	•	•

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

^[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 8. Characteristics

 $T_i = 25$ °C unless otherwise specified.

•						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Transistor	TR1					
I _{CBO}	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 \text{ °C}$	-	-	-5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$	100	-	-	
		$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$	100	-	800	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-75	-300	mV
		$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$	-	-250	-650	mV

BCV62

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Table 8. Characteristics ...continued $T_i = 25$ °C unless otherwise specified.

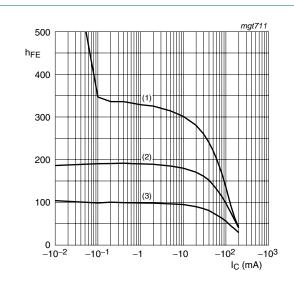
Symbol	Parameter	Conditions	Mir	n Typ	Max	Unit
V_{BEsat}	base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	<u>[1]</u> -	-700	-	mV
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	<u>[1]</u> -	-850	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	<u>[2]</u> –60	00 –650	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	[2] _	-	-820	mV
f _T	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	100) -	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}$	-	4.5	-	pF
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_C = -200 \mu\text{A}; R_S = 2 \text{ k}\Omega;$ f = 1 kHz; B = 200 Hz	-	-	10	dB
Transisto	r TR2					
V_{EBS}	emitter-base voltage	$V_{CB} = 0 \text{ V}; I_{E} = -250 \text{ mA}$	-	-	-1.5	V
		V_{CB} = 0 V; I_E = -10 μA	-40	00 -	-	mV
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -2 \text{ mA}$				
	BCV62		100) -	800	
	BCV62A		100) -	250	
	BCV62B		220) -	475	
	BCV62C		420) -	800	
Transisto	rs TR1 and TR2					
I_{C1}/I_{E2}	current matching	$I_{E2} = -0.5 \text{ mA};$ $V_{CE1} = -5 \text{ V};$				
		$T_{amb} \le 25 ^{\circ}C$	0.7	-	1.3	
		$T_{amb} \le 150 ^{\circ}C$	0.7	-	1.3	
I _{E2}	emitter current 2	$V_{CE1} = -5 \text{ V}$	[3] _	-	-5	mΑ

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] Device, without emitter resistors, mounted on an FR4 PCB.

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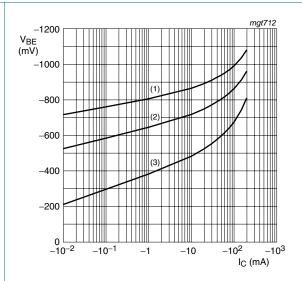
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 1. BCV62A: DC current gain as a function of collector current; typical values



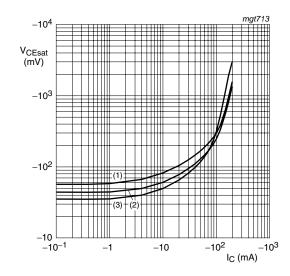
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 2. BCV62A: Base-emitter voltage as a function of collector current; typical values



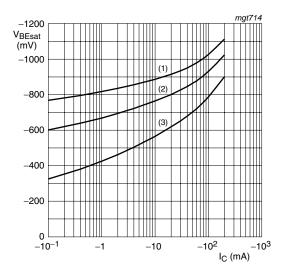
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. BCV62A: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

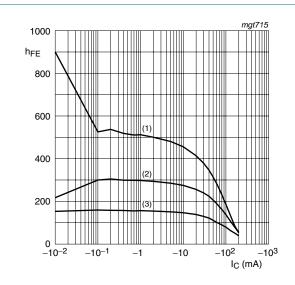
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. BCV62A: Base-emitter saturation voltage as a function of collector current; typical values

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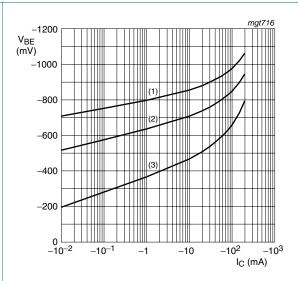
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. BCV62B: DC current gain as a function of collector current; typical values



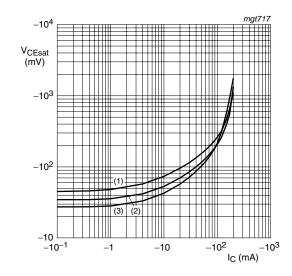
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. BCV62B: Base-emitter voltage as a function of collector current; typical values



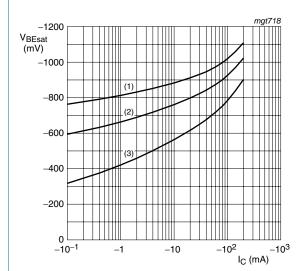
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. BCV62B: Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

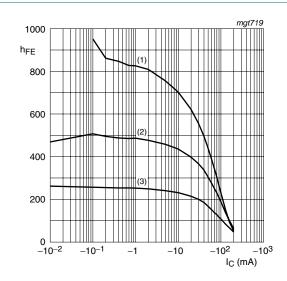
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 8. BCV62B: Base-emitter saturation voltage as a function of collector current; typical values

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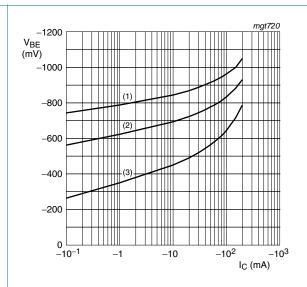
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. BCV62C: DC current gain as a function of collector current; typical values



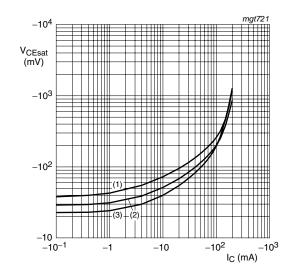
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. BCV62C: Base-emitter voltage as a function of collector current; typical values



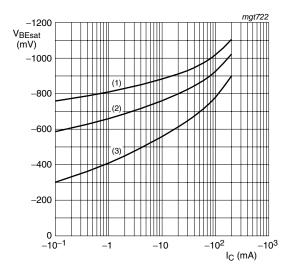
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. BCV62C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

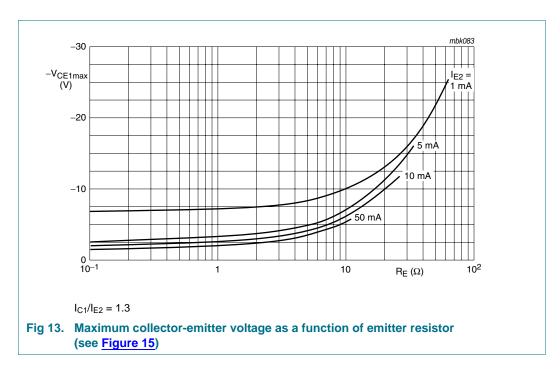
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

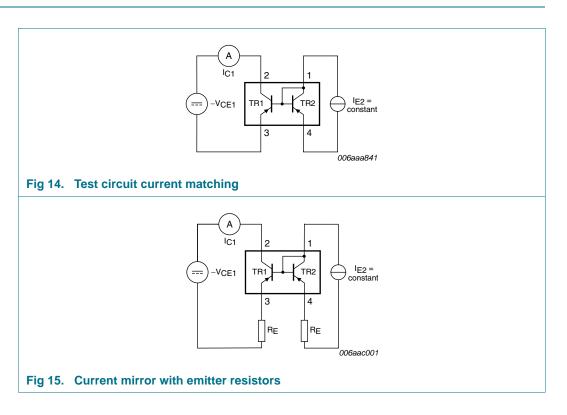
(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 12. BCV62C: Base-emitter saturation voltage as a function of collector current; typical values

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8. Test information

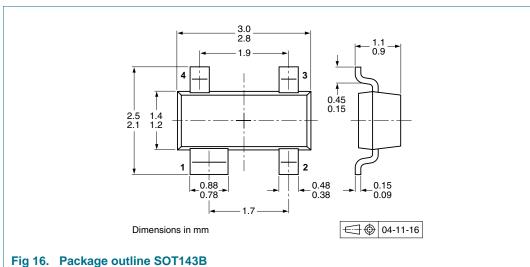


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8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Package outline 9.



10. Packing information

Table 9. **Packing methods**

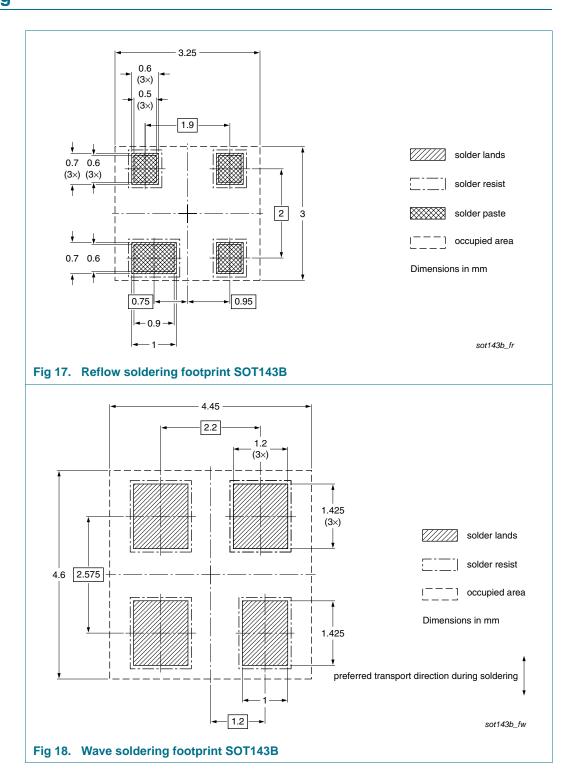
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity		
				3000	10000	
BCV62	SOT143B	SOT143B 4 mm pitch, 8 mm tape and reel	-215	-235		
BCV62A						
BCV62B						
BCV62C						

^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BCV62 v.4	20100726	Product data sheet	-	BCV62_3			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	 Legal texts have been adapted to the new company name where appropriate. 						
	Section 1 "Product profile": amended						
	Section 3 "Ordering information": added						
	Section 4 "Marking": updated						
	• Figure 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 and 12: added						
	Section 8 "Test information": added						
	• Figure 16: superseded by minimized package outline drawing						
	Section 10 "Packing information": added						
	Section 11 '	"Soldering": added					
	Section 13	"Legal information": updated	d				
BCV62_3	19990408	Product specification	-	BCV62_CNV_2			
BCV62_CNV_2	19970618	Product specification	-	-			

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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14. Contact information

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KW40Z FRDM-MC-LVBLDC PESD18VF1BSFYL PMF63UNEX PSMN4R0-60YS,115 HEF4028BPN RAPPID-567XFSW

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BZT52H-B9V1.115 BZV85-C3V9.113 BZX79-C47.113 P5020NSE7VNB S12ZVML12EVBLIN SCC2692AC1N40 LPC1785FBD208K

LPC2124FBD64/01 LS1020ASN7KQB LS1020AXN7HNB LS1020AXN7KQB LS1043ASE7PQA T1023RDB-PC FRDM-KW24D512